

NXPSC16650

Silicon Carbide Diode Rev.02 - 30 October 2019

Product data sheet

1. General description

Silicon Carbide Schottky diode in a TO220-2L plastic package, designed for high frequency switched-mode power supplies.



2. Features and benefits

- · Highly stable switching performance
- High forward surge capability I_{FSM}
- Extremely fast reverse recovery time
- Superior in efficiency to Silicon Diode alternatives
- Reduced losses in associated MOSFET
- Reduced EMI
- Reduced cooling requirements
- RoHS compliant

3. Applications

- Power factor correction
- Telecom / Server SMPS
- UPS
- PV inverter
- PC Silverbox
- LED / OLED TV
- Motor Drives

4. Quick reference data

Table 1. Q	uick reference data						
Symbol	Parameter	Conditions	Values			Unit	
Absolute	maximum rating						
V_{RRM}	repetitive peak reverse voltage			65	50		V
$I_{F(AV)}$	average forward current	δ = 0.5 ; square-wave pulse; T _{mb} ≤ 105 °C; Fig. 1; Fig. 2; Fig. 3	16		A		
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static ch	aracteristics						
V _F forward voltage		I _F = 16 A; T _j = 25 °C; <u>Fig. 5</u>		-	1.5	1.7	V
		I _F = 16 A; T _j = 150 °C; <u>Fig. 5</u>		-	1.8	2.1	V

5. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	
2	А	anode	$1 \qquad 7 \bigcirc 5$	K — A 001aaa020
mb	К	mounting base; connected to cathode		

6. Ordering information

Table 3. Ordering information								
Type number	Package name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date		
NXPSC16650	TO220-2L	NXPSC166506Q	Tube	50	SOD59A	30-Mar-2015		

7. Marking

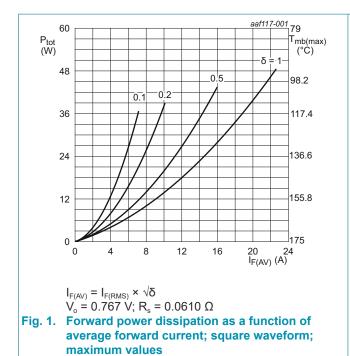
Table 4. Marking codes					
Type number	Marking codes				
NXPSC16650	NXPSC 16650				

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{RRM}	repetitive peak reverse voltage		650	V
V _{RWM}	crest working reverse voltage		650	V
V _R	reverse voltage	DC	650	V
$I_{F(AV)}$	average forward current	δ = 0.5; square-wave pulse; T _{mb} ≤ 105 °C; Fig. 1; Fig. 2; Fig. 3	16	A
I _{FRM}	repetitive peak forward current	δ = 0.5; t _p = 25 μs; T _{mb} ≤ 105 °C; square-wave pulse	32	A
I _{FSM}	non-repetitive peak	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	96	А
	forward current	t_p = 10 µs; $T_{j(init)}$ = 25 °C; square-wave pulse	770	А
l ² t	I ² t for fusing	sine-wave pulse; $T_{j(init)}$ = 25 °C; t_p = 10 ms	46	A ² s
T _{stg}	storage temperature		-55 to 175	°C
T _j	junction temperature		175	°C



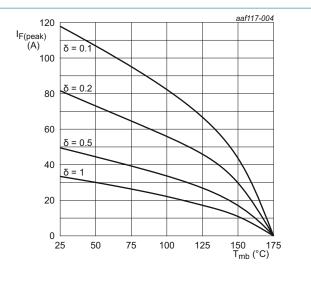
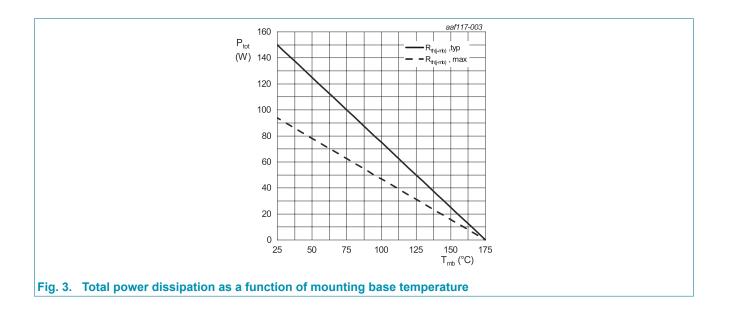


Fig. 2. Current derating as a function of mounting base temperature

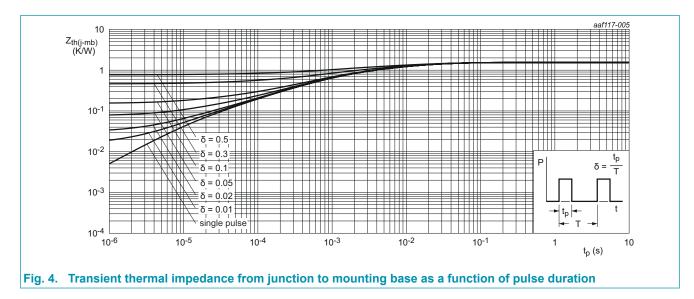
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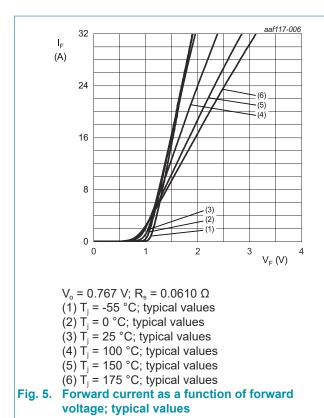
9. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th(j-mb)}}$	thermal resistance from junction to mounting base	with heatsink compound; Fig. 4	-	1	1.6	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient free air	in free air	-	60	-	K/W



10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V _F	forward current	I _F = 16 A; T _j = 25 °C; <u>Fig. 5</u>	-	1.5	1.7	V
		I _F = 16 A; T _j = 150 °C; <u>Fig. 5</u>	-	1.8	2.1	V
I _R	reverse current	V _R = 650 V; T _j = 25 °C; <u>Fig. 6</u>	-	-	100	μA
		V _R = 650 V; T _j = 150 °C; <u>Fig. 6</u>	-	-	400	μA
Dynamic	characteristics	· · · ·				
Q _r	recovered charge	I _F = 16 A; V _R = 400 V; dI _F /dt = 500 A/μs; T _j = 25 °C; <u>Fig. 7</u>	-	26	-	nC
C _d	diode capacitance	f = 1 MHz; V _R = 1 V; T _j = 25 °C	-	534	-	pF
		f = 1 MHz; V _R = 300 V; T _j = 25 °C	-	75	-	pF
		f = 1 MHz; V _R = 600 V; T _j = 25 °C	-	73	-	pF
E _{as}	non-repetitive	I _R = 6.9 A; L = 5 mH; T _{j(init)} = 25 °C	120	-	-	mJ
	avalanche energy					



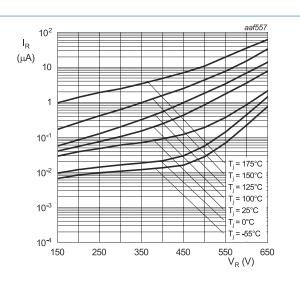
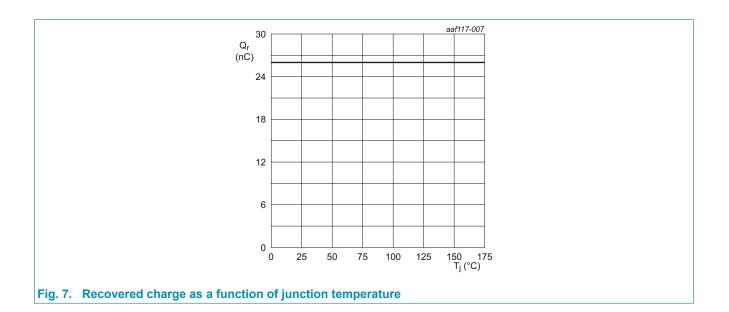
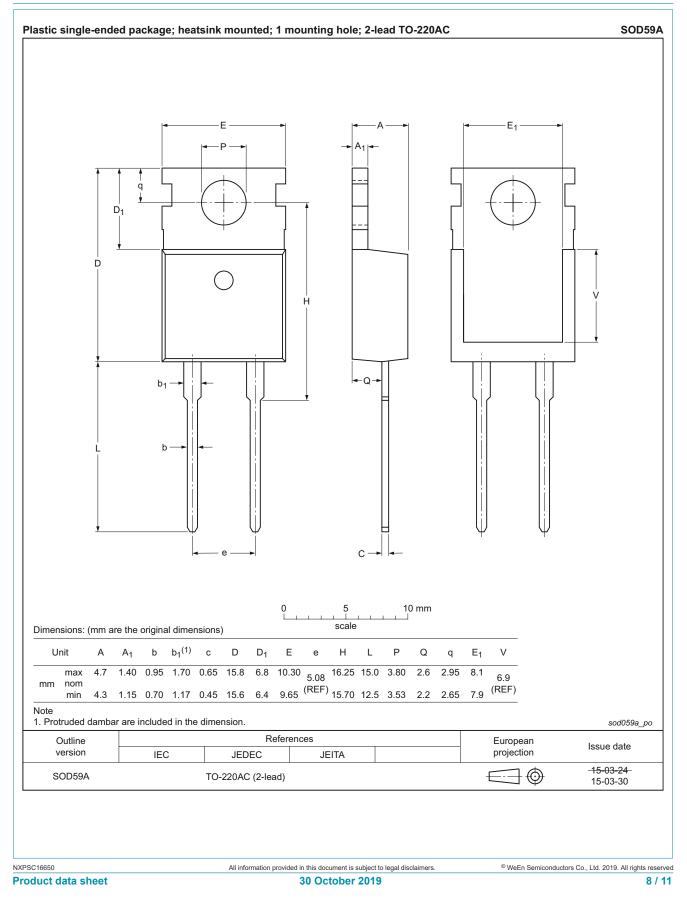


Fig. 6. Reverse leakage current as a function of reverse voltage; typical value

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11. Package outline



12. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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